

/ Descriptions

TO-252

P

P-CHANNEL MOSFET in a TO-252 Plastic Package.

/ Features

 $V_{DS} (V) = -60V$ $I_D = -20A$ ($V_{GS} = 20V$) $R_{DS(ON)} @ -10V$ 75m Ω (Typ. 62m Ω) $R_{DS(ON)} @ -4.5V \leq 100m\Omega$ (Typ. 70m Ω)

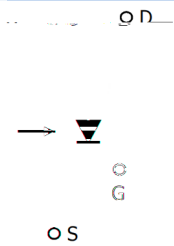
HF Product.

/ Applications

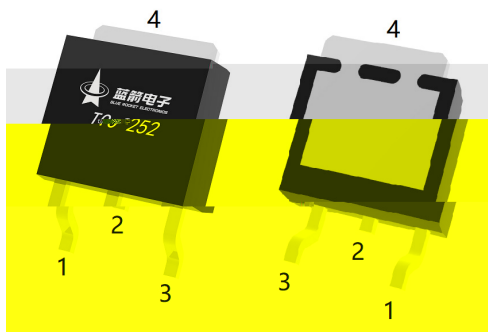
DC/DC

Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products.

/ Equivalent Circuit



/ Pinning



PIN1 G

PIN 2 D

PIN 3 S

PIN 4 D

/ Marking

See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	-60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current	$I_D (T_c=25^\circ\text{C})$	-20	A
Pulsed Drain Current	I_{DM}	-80	A
Avalanche Current	I_{AS}	-13.8	A
Avalanche energy L=0.5mH	E_{AS}	95	mJ
Power Dissipation for Single Operation	$P_D (T_c=25^\circ\text{C})$	45	W
Maximum Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	
Thermal Resistance-Junction to Ambient	R_{JA}	50	/W
Thermal Resistance- Junction-to-Case	R_{JC}	2.8	/W

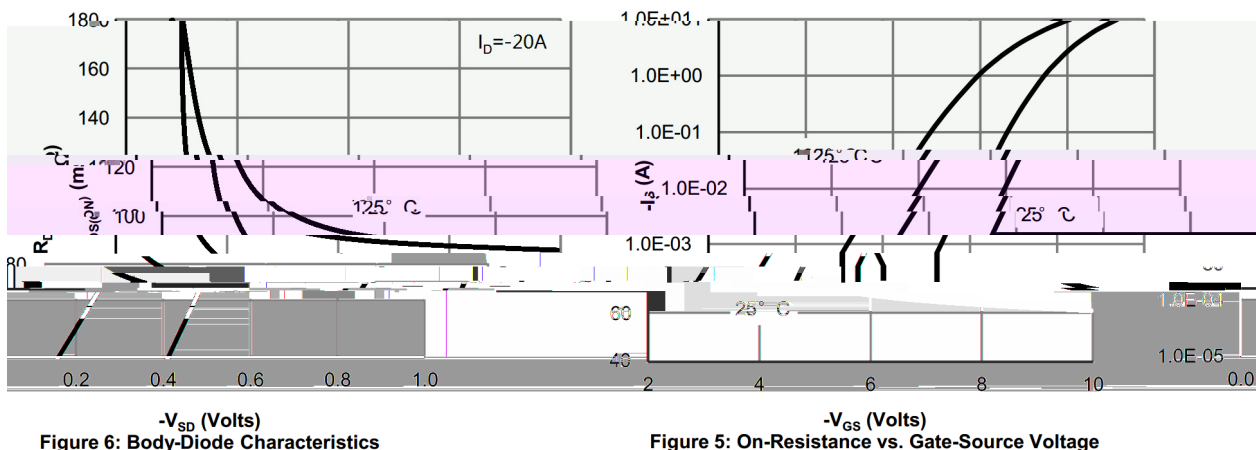
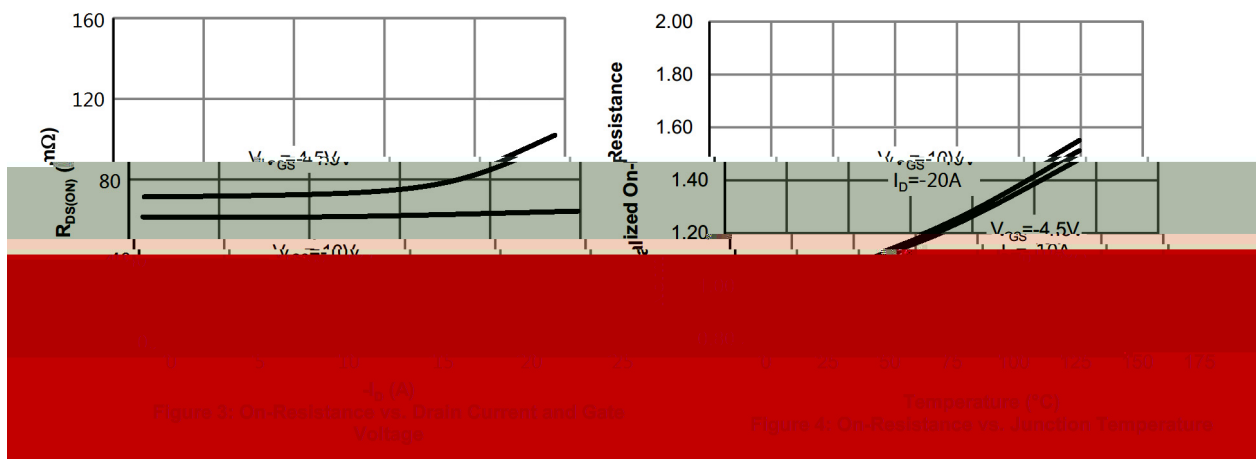
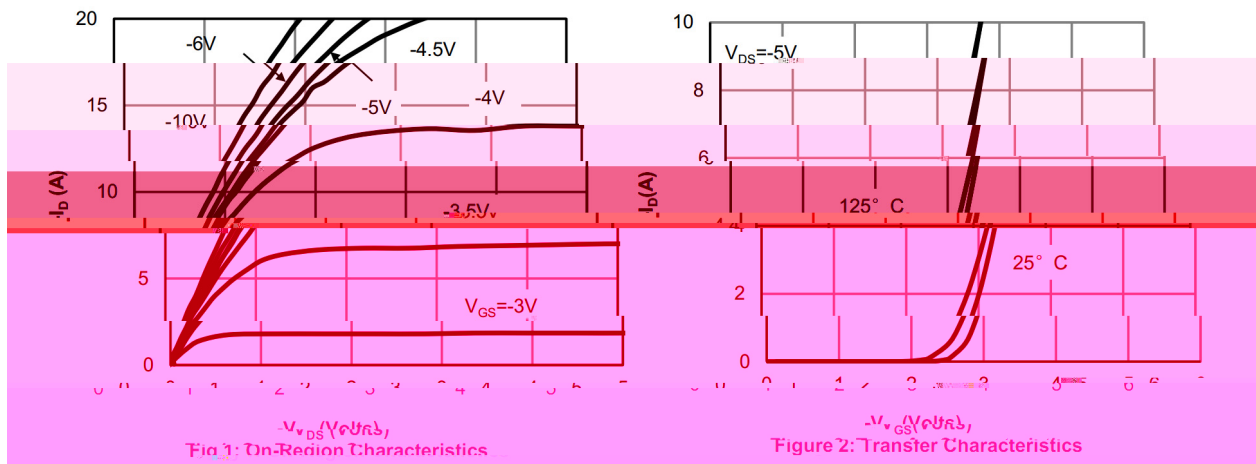
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=-250\text{ A}$ $V_{GS}=0\text{V}$	-60	-69		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-60\text{V}$ $V_{GS}=0\text{V}$			-1.0	
Gate-Body leakage current	I_{GSS}	$V_{DS}=0\text{V}$ $V_{GS}=\pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=-250\text{ A}$	-1.0	-1.5	-2.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=-10\text{V}$ $I_D=-20\text{A}$		62	75	m Ω
		$V_{GS}=-4.5\text{V}$ $I_D=-10\text{A}$		70	100	
Diode Forward Voltage	V_{SD}	$I_S=-1\text{A}$ $V_{GS}=0\text{V}$			-1.0	V
Input Capacitance	C_{iss}	$V_{GS}=0\text{V}$ $V_{DS}=-25\text{V}$ $f=1\text{MHz}$		1380		pF
Output Capacitance	C_{oss}			100		
Reverse Transfer Capacitance	C_{rss}			65		
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=-10\text{V}$ $V_{DS}=-30\text{V}$ $I_D=-4\text{A}$		20.8		nC
Total Gate Charge	$Q_{g(4.5V)}$			10.8		
Gate-Source Charge	Q_{gs}			3.5		
Gate-Drain Charge	Q_{gd}			3.6		

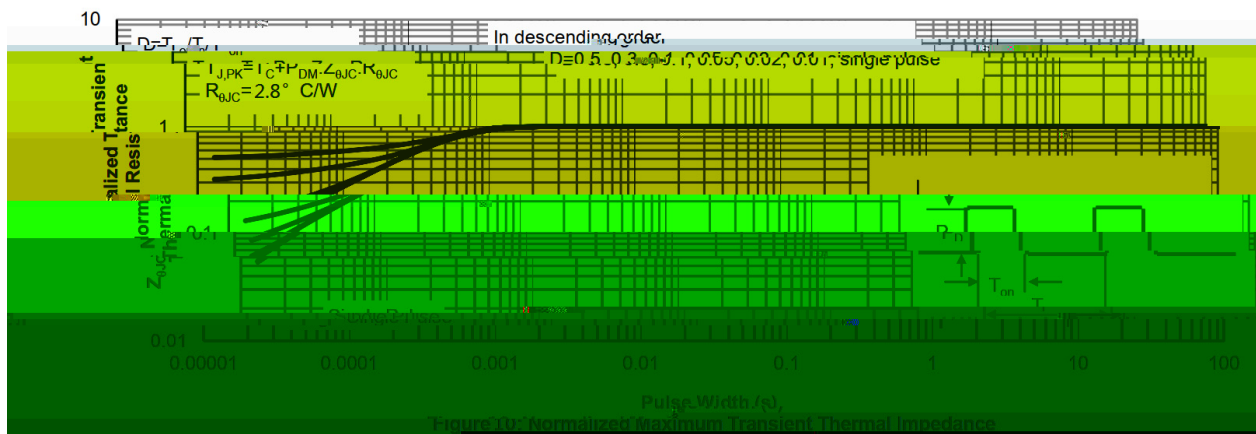
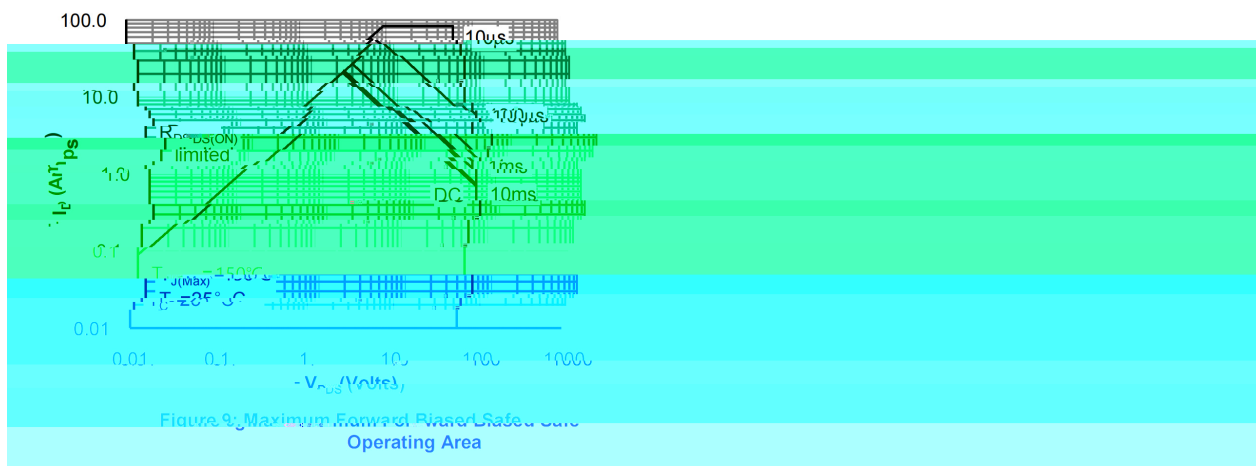
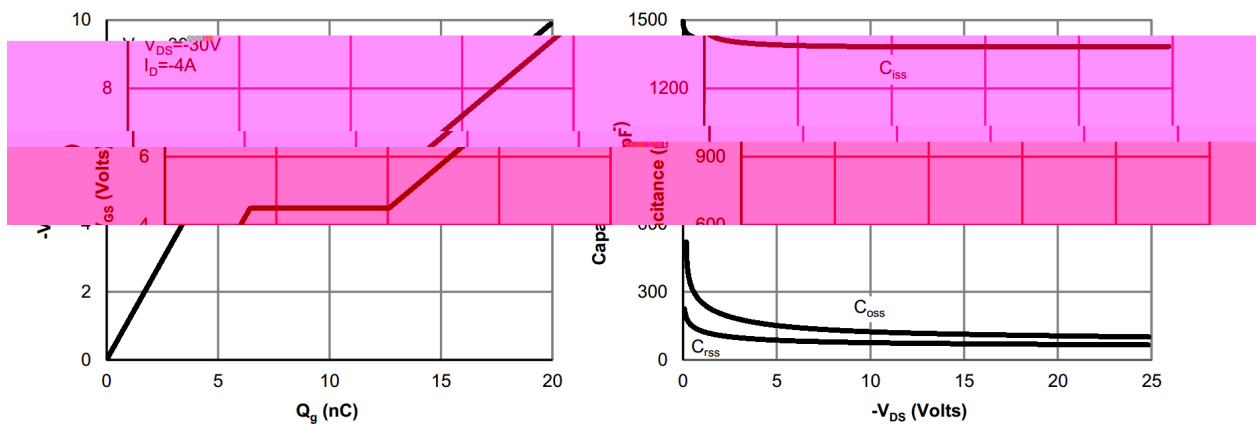
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-on Delay Time	$t_{d(ON)}$	$V_{GS}=-10V$ $V_{DS}=-30V$ $R_L=7.5$ $R_{GEN}=3$		8		ns
Turn-on Rise Time	t_r			3.8		
Turn-off Delay Time	$t_{d(OFF)}$			31.5		
Turn-off Fall Time	t_f			7.5		

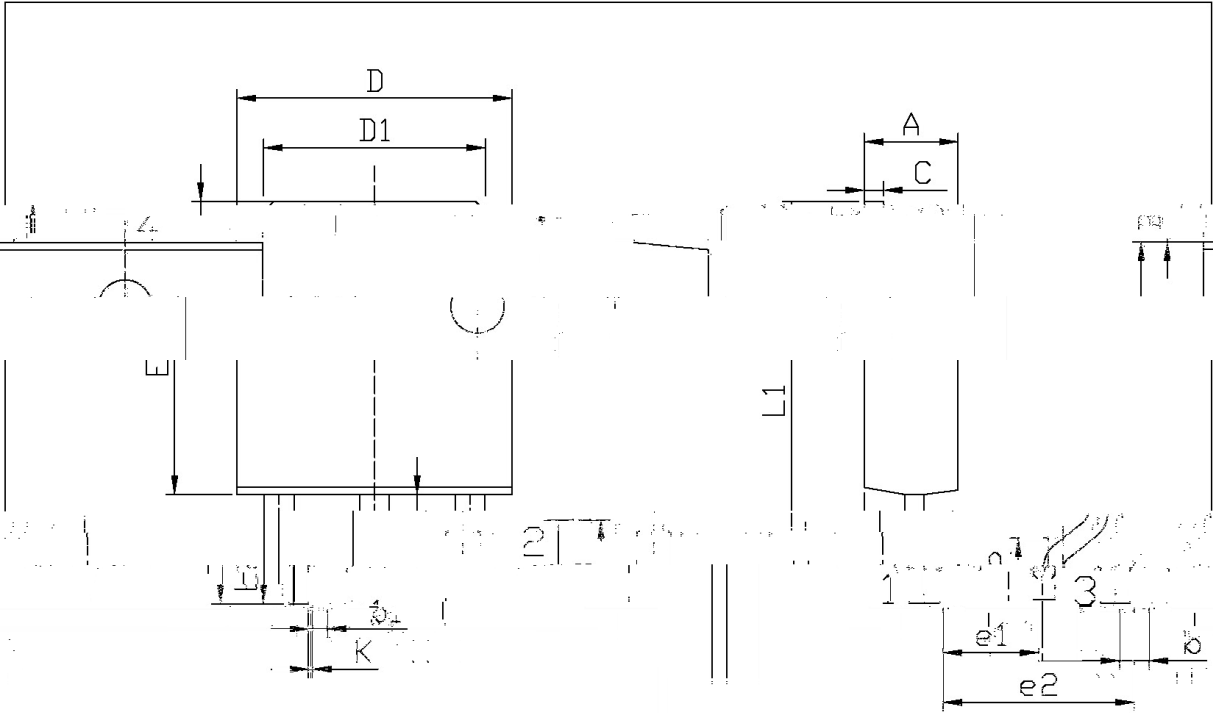
/ Electrical Characteristic Curve



/ Electrical Characteristic Curve



/ Package Dimensions



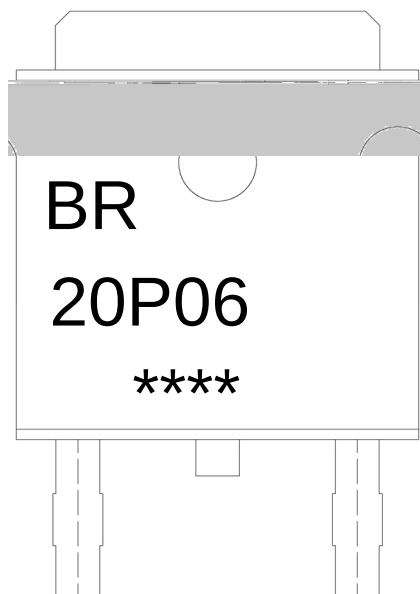
单位: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	2.20	2.40	E	5.95	6.25
B	0.95	1.25	e1	2.24	2.34
b	0.50	0.90	e2	4.43	4.73
b1	0.45	0.55	L1	9.45	9.95
C	0.45	0.55	L2	1.25	1.75
D	6.45	6.75	L3	0.60	0.90
D1	5.10	5.50	K	0.00	0.10

T0-252



/ Marking Instructions



BR

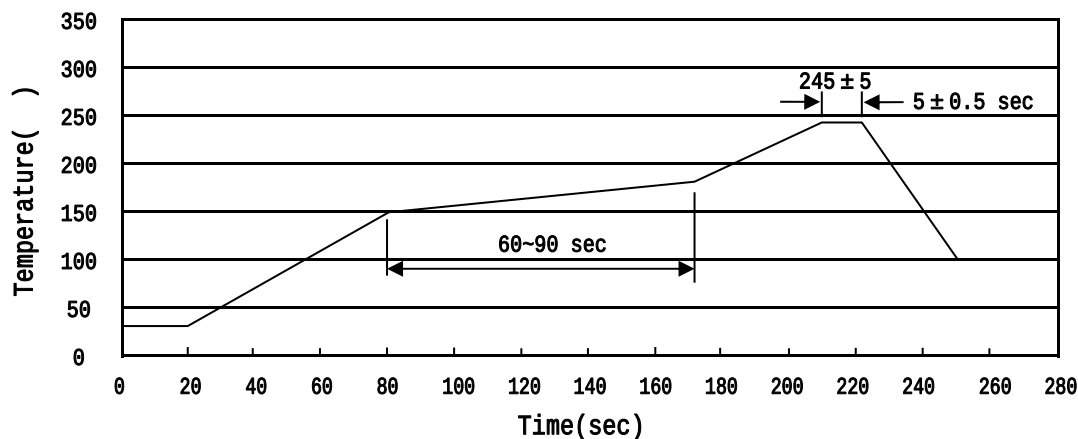
20P06

Note:

BR: Company Code

20P06: Product Type Code

****: Lot No. Code, code change with Lot No


() / Temperature Profile for IR Reflow Soldering(Pb-Free)


Note:

- | | | | | | |
|---|-------|-----|----|------------|---|
| 1 | 150 | 180 | 60 | 90sec; | 1.Preheating:150~180 °C, Time:60~90sec. |
| 2 | 245±5 | | | 5±0.5sec; | 2.Peak Temp.:245±5 °C, Duration:5±0.5sec. |
| 3 | | | 2 | 10 °C/sec. | 3. Cooling Speed: 2~10 °C/sec. |

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.
/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
TO-252	2,500	2	5,000	6	30,000	13 ×16	360×360×50	380×335×366

/ TUBE

Package Type	Units					Dimension (unit mm ³)		
	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Tube	Inner Box	Outer Box
TO-251/252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180

/ Notices